

**In the Specification**

Please substitute the first paragraph on page 33 through the third paragraph on page 34 with the following paragraphs.

C1 For this approximate physical model, we consider the substrate as three equal layers each of thickness  $\Delta h/3$ . We estimate the temperature rise of the top, directly heated layer and then compare this to an estimate of the heat transferred through the middle layer to the back layer to give an upper value for the exposure time  $t_E$  to the heat flux that gives a large temperature differential through the thickness. If the top layer were thermally isolated, equation (6) gives the temperature rise  $\Delta T$  for the exposure time  $t_E$  with an input heating power  $W$  to the top layer of thickness  $\Delta h/3$  as:

$$(14) \quad \Delta T = 3W t_E / \rho c_p \Delta h$$

We now estimate the heat transferred through the middle layer, thickness  $\Delta h/3$ , to the back layer during the exposure time  $t_E$ . We use equation (145) to estimate the temperature difference across the middle layer as  $\Delta T/4$  (e.g.,  $\sim \Delta T/2$  for the top layer,  $\sim 1/2(\Delta T/2)$  for both middle and bottom layers. For there to be a large temperature difference through the wafer thickness when exposure to the heat flux has ended, the heat transferred to the back layer must be significantly smaller than the heat input into the front surface.

As an upper value for estimating onset of the regime for a large temperature differential, Equation (13) then gives for the heat transfer from the top layer to through the middle layer to the back layer as:

$$(\text{area}) W = k (\text{area}) (\Delta T/4) / (\Delta h/3)$$

$$(15) \quad W = (3/4)k\Delta T/\Delta h$$

Substituting for  $\Delta T$  from equation (14) and solving for  $t_E$  gives the estimate for the upper bound to the exposure time for the regime with a large temperature differential as:

$$(16) \quad t_E < (4/9)\rho c_p \Delta h^2 / k$$

We note that this expression does not explicitly contain the input heating power; however since the heat capacity  $c_p$  and the thermal conductivity  $k$  are somewhat temperature dependent for all materials there is an implicit dependence on the heat input by way of the temperature dependence of these variables.

For the case of a silicon wafer for heating to a peak temperature above 1200 degrees C, representative values for the variables in (16) are:  $\rho = 2.33 \times 10^3 \text{ Kg/m}^3$ ;  $c_p = 700 \text{ J/(kg degrees C)}$ ;  $\Delta h = .75 \times 10^{-3} \text{ m}$  and  $k = 40 \text{ W/(m degrees C)}$  which give:

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